Ordering number:EN1072D

NPN Triple Diffused Planar Silicon Transistor

2SC3153

800V/6A Switching Regulator Applications

Features

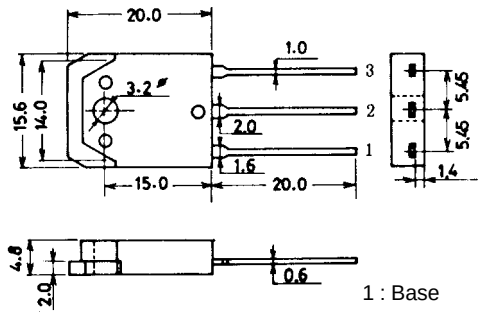
- High breakdown voltage (V_{CBO}≥900V).
- Fast switching speed.
- Wide ASO.

Package Dimensions

unit:mm

2022A

[2SC3153]



1 : Base
2 : Collector
3 : Emitter
SANYO : TO-3PB

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		900	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		6	A
Collector Current (Pulse)	I_{CP}	Pulse, PW≤300μs, Duty Cycle≤10%	20	A
Base Current	I_B		3	A
Collector Dissipation	P_C	Tc=25˚C	100	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=800V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}1$	V_{CE}=5V, I_C=0.4A	10*		40*	
	$h_{FE}2$	V_{CE}=5V, I_C=2A	8			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.4A		15		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		120		pF

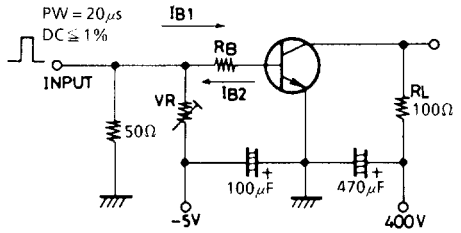
* : For the $h_{FE}1$ of the 2SC3153, specify two ranks or more in principle.

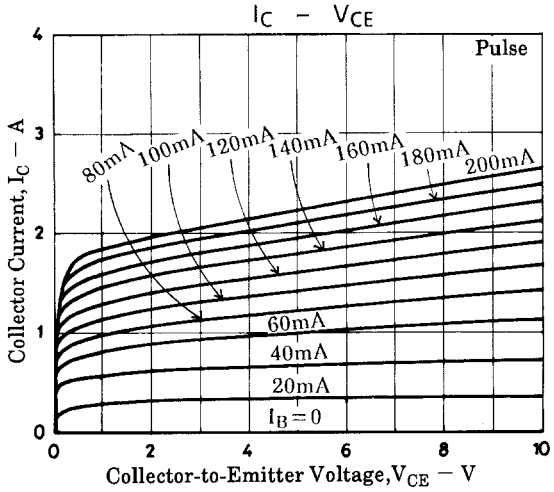
10 K 20	15 L 30	20 M 40

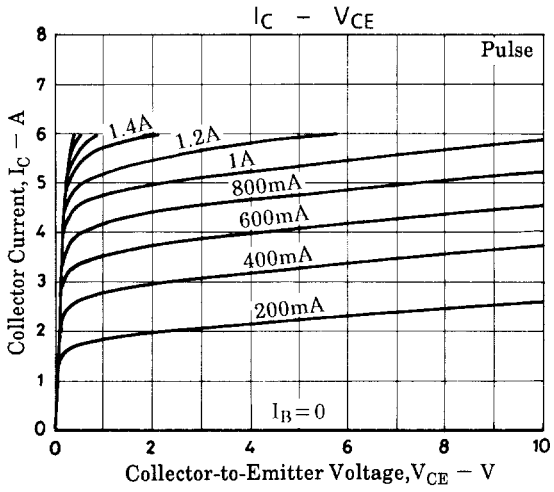
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

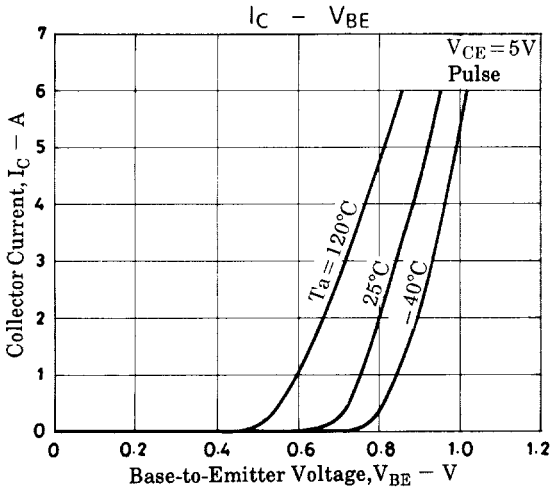
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=0.6A			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=3A, I_B=0.6A			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	900			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, R_{BE}=∞	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEO(sus)}$	I_C=6A, L=200μH, I_B=2A	800			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)1}$	I_C=2A, I_{B1}=0.4A, I_{B2}=–0.4A, L=1mH, clamped	800			V
	$V_{CEX(sus)2}$	I_C=1A, I_{B1}=0.2A, I_{B2}=–0.2A, L=2mH, clamped	900			V
Turn-ON Time	t_{on}	I_C=4A, I_{B1}=0.8A, I_{B2}=–1.6A, R_L=100Ω, V_{CC}=400V			1.0	μs
Storage Time	t_{stg}	I_C=4A, I_{B1}=0.8A, I_{B2}=–1.6A, R_L=100Ω, V_{CC}=400V			3.0	μs
Fall Time	t_f	I_C=4A, I_{B1}=0.8A, I_{B2}=–1.6A, R_L=100Ω, V_{CC}=400V			0.7	μs

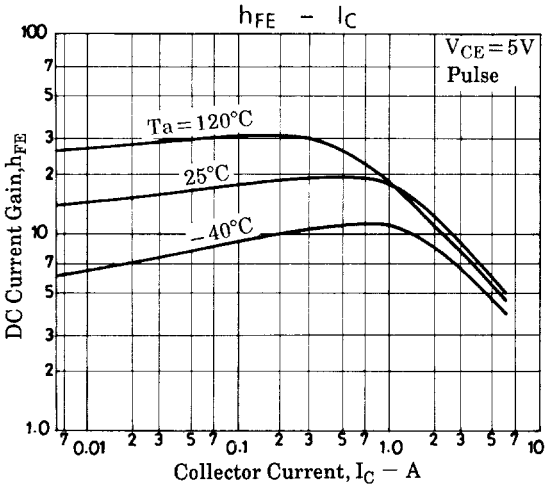
Switching Time Test Circuit



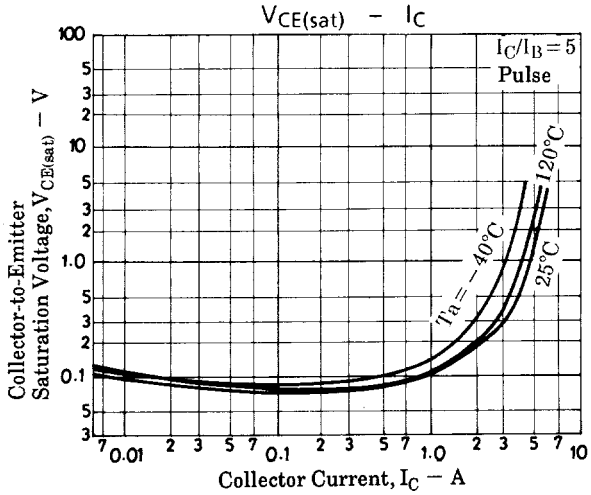




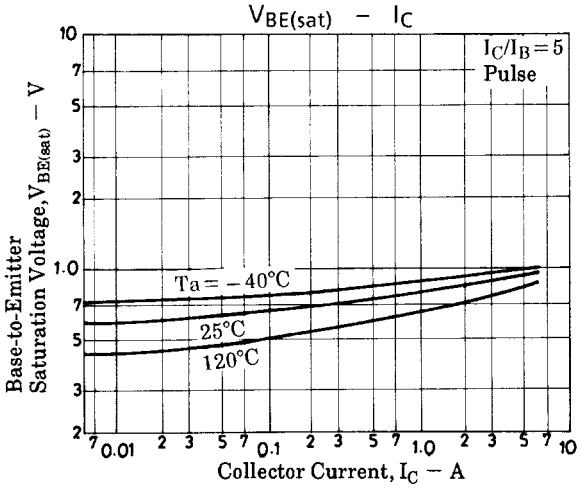




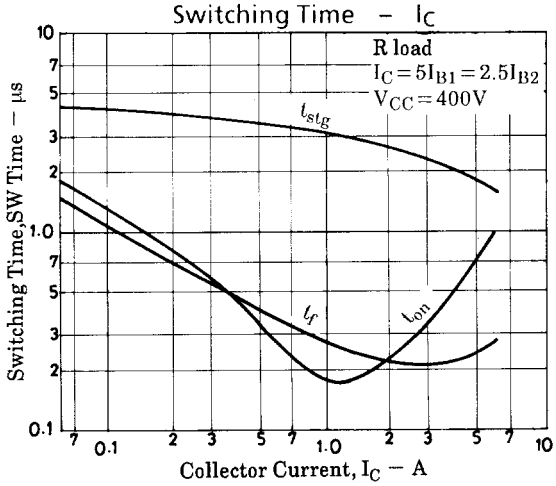
$V_{CE(sat)}$ – I_C



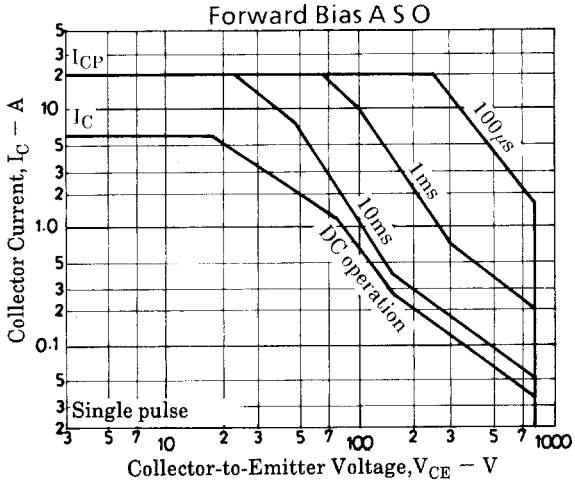
$V_{BE(sat)}$ – I_C



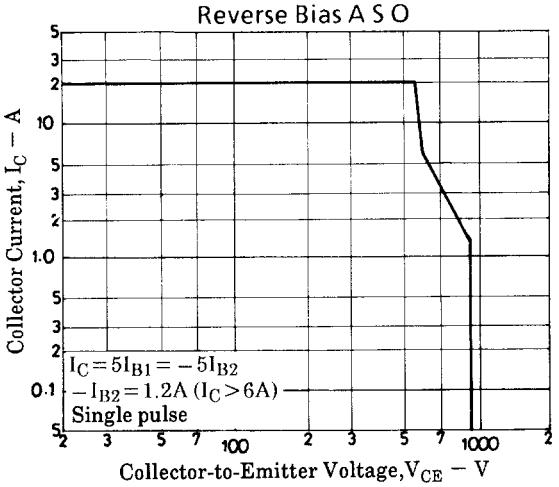
Switching Time – I_C



Forward Bias A S O



Reverse Bias A S O



P_C – Tc